



SBT3906

PNP Silicon Transistor

Descriptions

- General small signal application
- Switching application

Features

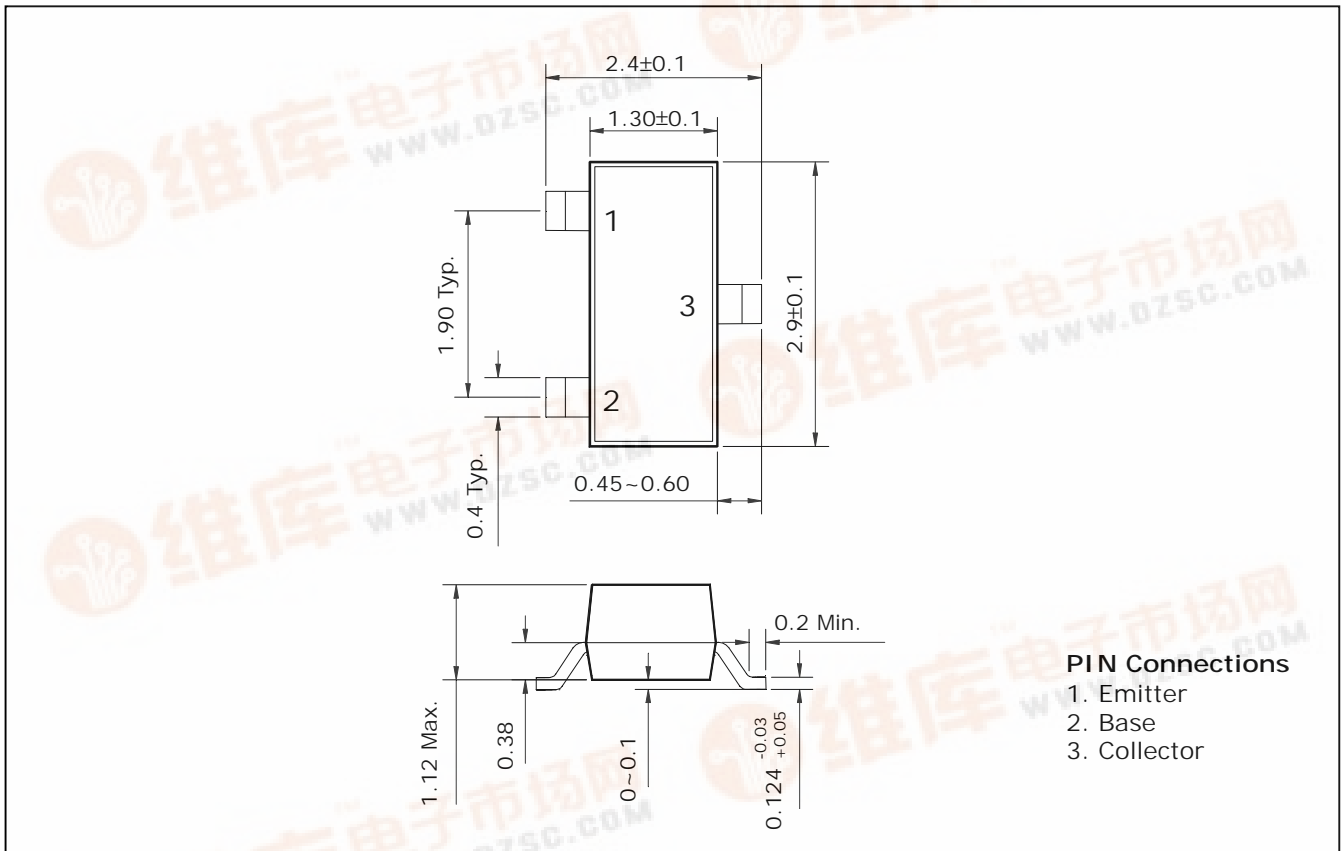
- Low collector saturation voltage
- Collector output capacitance
- Complementary pair with SBT3904

Ordering Information

Type NO.	Marking	Package Code
SBT3906	2A	SOT-23

Outline Dimensions

unit : mm



Absolute maximum ratings

Ta=25°C

Characteristic	Symbol	Ratings	Unit
Collector-Base voltage	V _{CBO}	-40	V
Collector-Emitter voltage	V _{CEO}	-40	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	I _C	-200	mA
Collector dissipation	P _C [*]	350	mW
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55 ~ 150	°C

* : Package mounted on 99.5% alumina 10×8×0.6mm

Electrical Characteristics

Ta=25°C

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base breakdown voltage	BV _{CBO}	I _C =-10μA, I _E =0	-40	-	-	V
Collector-Emitter breakdown voltage	BV _{CEO}	I _C =-1mA, I _B =0	-40	-	-	V
Emitter-Base breakdown voltage	BV _{EBO}	I _E =-10μA, I _C =0	-5	-	-	V
Collector cut-off current	I _{CEX}	V _{CE} =-30V, V _{EB} =-3V	-	-	-50	nA
DC current gain	h _{FE}	V _{CE} =-1V, I _C =-10mA	100	-	300	-
Collector-Emitter saturation voltage	V _{CE(sat)}	I _C =-50mA, I _B =-5mA	-	-	-0.4	V
Transition frequency	f _T	V _{CE} =-20V, I _C =-10mA, f=100MHz	250	-	-	MHz
Collector output capacitance	C _{ob}	V _{CB} =-5V, I _E =0, f=1MHz	-	-	4.5	pF
Delay time	t _d	V _{CC} =-3V _{dc} , V _{BE(off)} =-0.5V _{dc} , I _C =-10mA _{dc} , I _{B1} =-1mA _{dc}	-	-	35	ns
Rise time	t _r		-	-	35	ns
Storage time	t _s	V _{CC} =-3V _{dc} , I _C =-10mA _{dc} , I _{B1} =I _{B2} =-1mA _{dc}	-	-	225	ns
Fall Time	t _f		-	-	75	ns

Electrical Characteristic Curves

Fig. 1 P_C - T_a

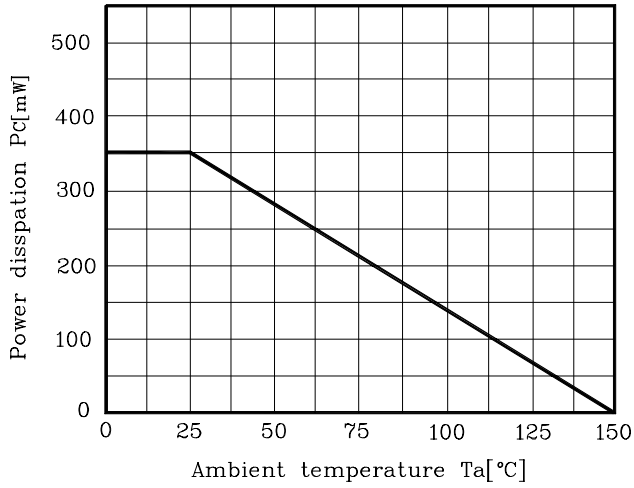


Fig. 2 h_{FE} - I_C

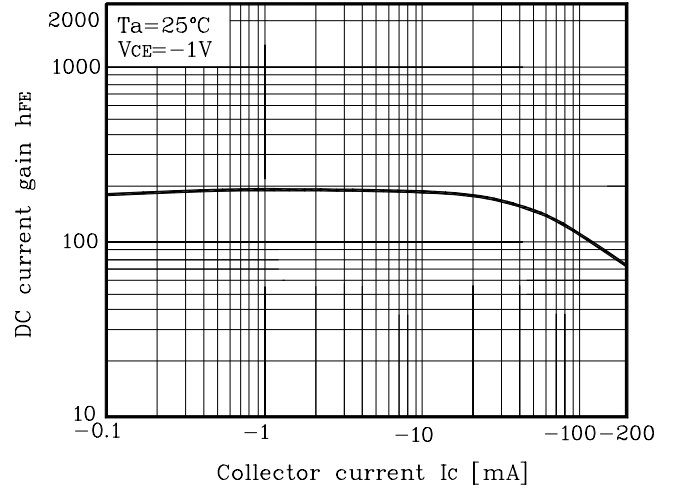


Fig. 3 $V_{CE(sat)}$ - I_C

